


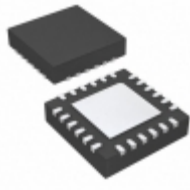
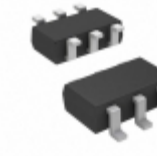



	<h2>SI3481DV-T1-E3</h2>
	<p>Hersteller-Teilenummer: SI3481DV-T1-E3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 30V 4A 6-TSOP</p> <p>Datenblätter:  SI3481DV-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 24152 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI3481DV-T1-E3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 30V 4A 6-TSOP
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	24152 pcs Stock
detaillierte Beschreibung	P-Channel 30V 4A (Ta) 1.14W (Ta) Surface Mount 6-
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	SOT-23-6 Thin, TSOT-23-6
Supplier Device-Gehäuse	6-TSOP
Verlustleistung (max)	1.14W (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4A (Ta)
Rds On (Max) @ Id, Vgs	48 mOhm @ 5.3A, 10V
VGS (th) (Max) @ Id	3V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	25nC @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI3481DV-T1-E3CT















































SI3481DV-T1-E3 ist neu im Original, Suche SI3481DV-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI3481DV-T1-E3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI3481DV-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI3481DV-T1-GE3 Vishay / Siliconix MOSFET P-CH 30V 4A 6-TSOP</p>	 <p>SI3481DV-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 4A 6-TSOP</p>	 <p>SI3482-A01-GM Energy Micro (Silicon Labs) IC CTRLR POE 24-48PORT PSE 24-QFN</p>	 <p>SI3481DV-T1-E3 Vishay / Siliconix MOSFET P-CH 30V 4A 6-TSOP</p>
 <p>SI3480-A01-GM Energy Micro (Silicon Labs) IC CTRLR 4/8-PORT POE 20-QFN</p>	 <p>SI3477DV-T1-GE3 Vishay / Siliconix MOSFET P-CH 12V 8A 6-TSOP</p>	 <p>SI3477DV-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 8A 6-TSOP</p>	 <p>SI3480MS8-KIT Energy Micro (Silicon Labs) KIT EVAL 8PORT SI3480/52/SI3500</p>

heiße Teile

Mehr

Contact us: Info@Y-IC.com

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